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MMUN2217L, NSVMMUN2217L

Digital Transistors (BRT) R1 = 4.7 k\Omega, R2 = 10 k Ω

NPN Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_A = 25^{\circ}C$)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector Current – Continuous	۱ _C	100	mAdc
Input Forward Voltage	V _{IN(fwd)}	20	Vdc
Input Reverse Voltage	V _{IN(rev)}	7	Vdc

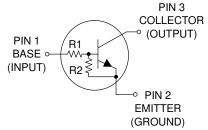
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



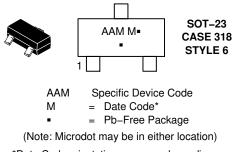
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MARKING DIAGRAM



*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

MMUN2217L, NSVMMUN2217L

Table 1. ORDERING INFORMATION

Device	Part Marking	Package	Shipping [†]
MMUN2217LT1G	AAM	SC–23 (Pb–Free)	3000 / Tape & Reel
NSVMMUN2217LT1G	AAM	SC–23 (Pb–Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

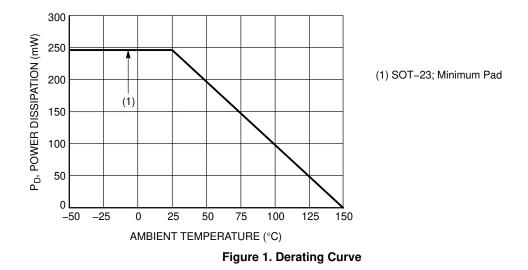


Table 2. THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit	
THERMAL CHARACTERISTICS (SOT-23) (MMUN2217L)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P _D	246 400 2.0 3.2	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 2) (Note 1) (Note 2)	R_{\thetaJA}	508 311	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{\theta JL}$	174 208	°C/W
Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C

1. FR-4 @ Minimum Pad. 2. FR-4 @ 1.0 x 1.0 Inch Pad.

MMUN2217L, NSVMMUN2217L

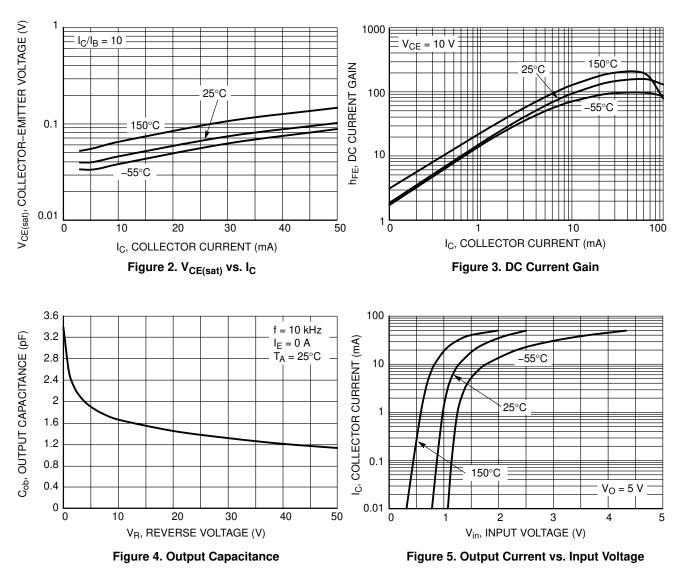
Table 3. ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$, unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$	I _{CBO}	_	-	100	nAdc
Collector–Emitter Cutoff Current $(V_{CE} = 50 \text{ V}, I_B = 0)$	I _{CEO}	_	-	500	nAdc
Emitter–Base Cutoff Current ($V_{EB} = 6.0 \text{ V}, I_C = 0$)	I _{EBO}	_	-	0.5	mAdc
Collector–Base Breakdown Voltage $(I_C = 10 \ \mu\text{A}, I_E = 0)$	V _{(BR)CBO}	50	_	-	Vdc
Collector–Emitter Breakdown Voltage (Note 3) $(I_{C} = 2.0 \text{ mA}, I_{B} = 0)$	V _{(BR)CEO}	50	_	-	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 3) ($I_C = 5.0 \text{ mA}, V_{CE} = 10 \text{ V}$)	h _{FE}	35	60	-	
Collector – Emitter Saturation Voltage (Note 3) ($I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$)	VCE(sat)	_	_	0.25	Vdc
Input Voltage (off) ($V_{CE} = 5.0 \text{ V}, I_C = 100 \mu \text{A}$)	V _{i(off)}	_	0.9	0.3	Vdc
Input Voltage (on) (V _{CE} = 0.3 V, I _C = 20 mA)	V _{i(on)}	2.5	2.0	-	Vdc
Output Voltage (on) (V_{CC} = 5.0 V, V_B = 2.5 V, R_L = 1.0 k\Omega)	V _{OL}	-	-	0.2	Vdc
Output Voltage (off) $(V_{CC} = 5.0 \text{ V}, \text{ V}_{B} = 0.5 \text{ V}, \text{ R}_{L} = 1.0 \text{ k}\Omega)$	V _{OH}	4.9	_	_	Vdc
Input Resistor	R1	3.3	4.7	6.1	kΩ
Resistor Ratio	R ₁ /R ₂	0.38	0.47	0.56	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

MMUN2217L, NSVMMUN2217L

TYPICAL CHARACTERISTICS MMUN2217L



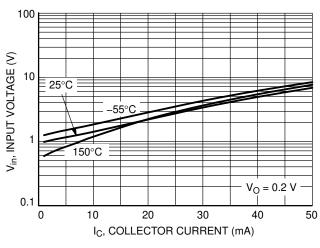
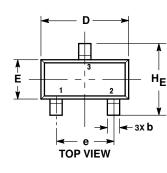


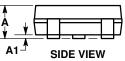
Figure 6. Input Voltage vs. Output Current

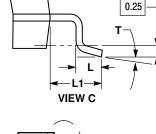
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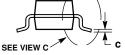
PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AR**









END VIEW

NOTES 2.

DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF 3. THE BASE MATERIAL. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,

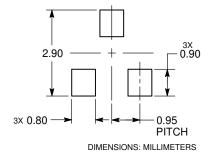
4 PROTRUSIONS, OR GATE BURRS

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Е	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10°	0°		10°

STYLE 6: PIN 1. BASE 2. EMITTER

COLLECTOR 3.

RECOMMENDED SOLDERING FOOTPRINT



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